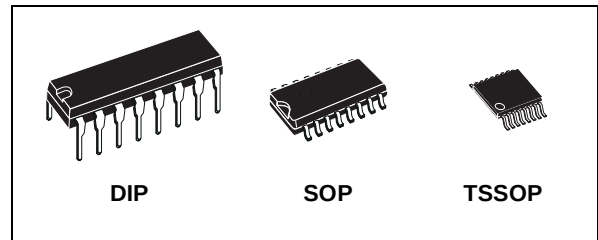




M74HC368

HEX BUS BUFFER WITH 3 STATE OUTPUT INVERTING

- HIGH SPEED:
 $t_{PD} = 9ns$ (TYP.) at $V_{CC} = 6V$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu A$ (MAX.) at $T_A = 25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 6mA$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH
74 SERIES 368



ORDER CODES

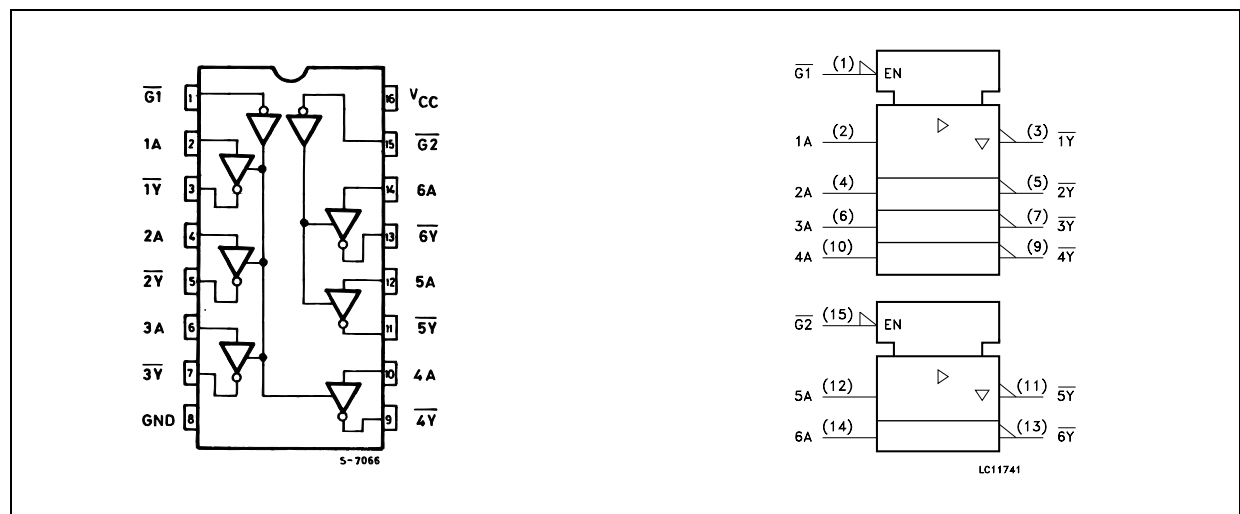
PACKAGE	TUBE	T & R
DIP	M74HC368B1R	
SOP	M74HC368M1R	M74HC368RM13TR
TSSOP		M74HC368TTR

DESCRIPTION

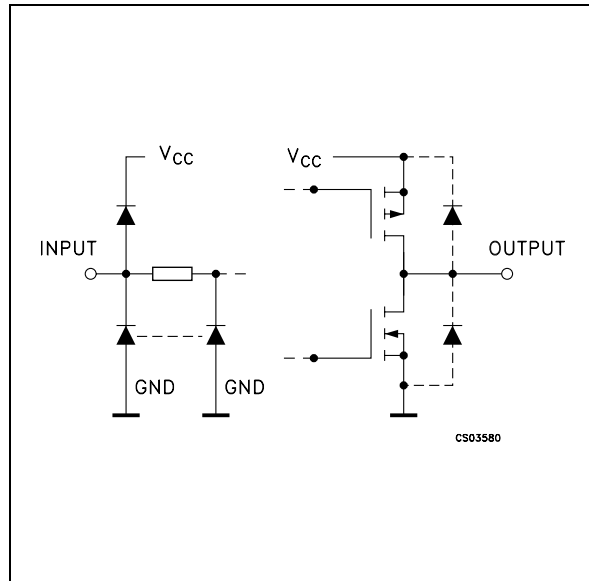
The M74HC368 is an high speed CMOS HEX BUS BUFFER 3-STATE OUTPUTS fabricated with silicon gate C²MOS technology. This device contains six buffers, four buffers are controlled by an enable input ($\overline{G1}$) and the other two buffers are controlled by the other enable input ($\overline{G2}$); the outputs of each buffer group are

enabled when $\overline{G1}$ and/or $\overline{G2}$ inputs are held low, and when held high, these outputs are disabled in a high-impedance state. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	$\overline{G1}, \overline{G2}$	3 State Output Enable Input
2, 4, 6, 10, 12, 14	1A to 6A	Data Inputs
3, 5, 7, 9, 11, 13	1Y to 6Y	Data Outputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUTS
$\overline{G}$	A _n	$\overline{Y_n}$
L	L	H
L	H	L
H	X	Z

X: Don't Care
Z: High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 35	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 70	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000
		V _{CC} = 4.5V	0 to 500
		V _{CC} = 6.0V	0 to 400

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C			
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V _{OH}	High Level Output Voltage	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		V	
		4.5	I _O =-20 μA	4.4	4.5		4.4		4.4			
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9			
		4.5	I _O =-6.0 mA	4.18	4.31		4.13		4.10			
		6.0	I _O =-7.8 mA	5.68	5.8		5.63		5.60			
V _{OL}	Low Level Output Voltage	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	V	
		4.5	I _O =20 μA		0.0	0.1		0.1		0.1		
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1		
		4.5	I _O =6.0 mA		0.17	0.26		0.33		0.40		
		6.0	I _O =7.8 mA		0.18	0.26		0.33		0.40		
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA	
I _{OZ}	High Impedance Output Leakage Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			± 0.5		± 5		± 10	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	Test Condition			Value							Unit
		V _{CC} (V)	C _L (pF)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0	50			25	60		75		90	ns
		4.5				7	12		15		18	
		6.0				6	10		13		15	
t _{PLH} t _{PHL}	Propagation Delay Time	2.0	50			30	85		105		130	ns
		4.5				10	17		21		26	
		6.0				9	14		18		22	
		2.0	150			42	105		130		160	ns
		4.5				14	21		26		32	
		6.0				12	18		22		27	
t _{PZL} t _{PZH}	High Impedance Output Enable Time	2.0	50	R _L = 1 KΩ		36	90		115		135	ns
		4.5				11	18		23		27	
		6.0				9	15		20		23	
		2.0	150	R _L = 1 KΩ		49	110		140		165	ns
		4.5				15	22		28		33	
		6.0				13	19		24		28	
t _{PLZ} t _{PHZ}	High Impedance Output Disable Time	2.0	50	R _L = 1 KΩ		32	95		120		145	ns
		4.5				14	19		24		29	
		6.0				12	16		20		25	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value							Unit
		V _{CC} (V)			T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance					5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)					33						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$ (per Channel)

Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050

